

## isc N-Channel MOSFET Transistor

AOD254

### • FEATURES

- Static drain-source on-resistance:  
 $R_{DS(on)} \leq 46m\Omega$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### • DESCRIPTION

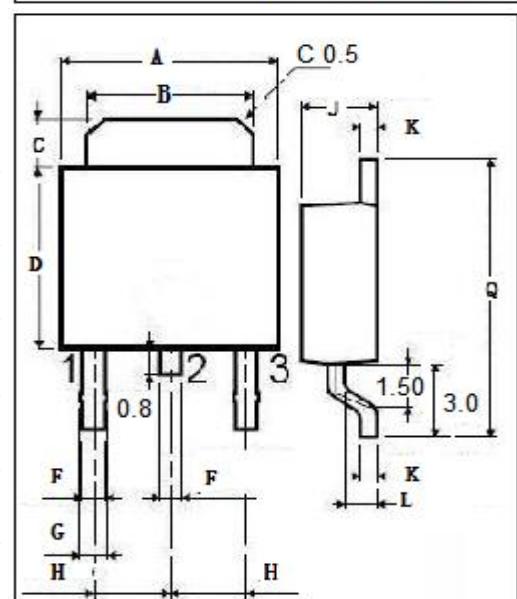
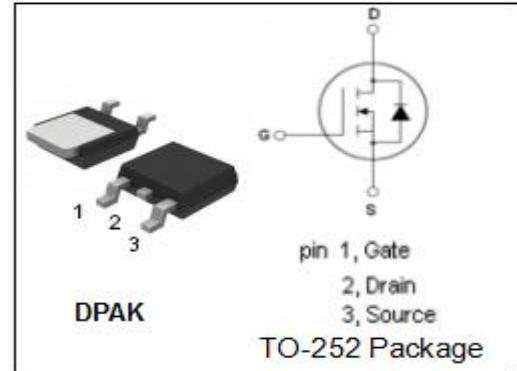
- Switching applications

### • ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

| SYMBOL    | PARAMETER                            | VALUE    | UNIT |
|-----------|--------------------------------------|----------|------|
| $V_{DSS}$ | Drain-Source Voltage                 | 150      | V    |
| $V_{GS}$  | Gate-Source Voltage                  | $\pm 20$ | V    |
| $I_D$     | Drain Current-Continuous             | 28       | A    |
| $I_{DM}$  | Drain Current-Single Pulsed          | 45       | A    |
| $P_D$     | Total Dissipation @ $T_c=25^\circ C$ | 100      | W    |
| $T_j$     | Max. Operating Junction Temperature  | 175      | °C   |
| $T_{stg}$ | Storage Temperature                  | -55~175  | °C   |

### • THERMAL CHARACTERISTICS

| SYMBOL        | PARAMETER                          | MAX | UNIT |
|---------------|------------------------------------|-----|------|
| $R_{th(j-c)}$ | Channel-to-case thermal resistance | 1.5 | °C/W |



**isc N-Channel MOSFET Transistor****AOD254****ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

| SYMBOL              | PARAMETER                      | CONDITIONS  | MIN | TYP | MAX  | UNIT |
|---------------------|--------------------------------|---|-----|-----|------|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> =250 μ A                      | 150 |     |      | V    |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =100 μ A        | 1.7 |     | 2.7  | V    |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> =10V; I <sub>D</sub> =20A                         |     |     | 46   | mΩ   |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> = ±20V  |     |     | ±100 | nA   |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> =150V; V <sub>GS</sub> = 0V                       |     |     | 1    | μ A  |
|                     |                                | V <sub>DS</sub> =150V; V <sub>GS</sub> = 0V; T <sub>c</sub> =55°C |     |     | 5    | μ A  |
| V <sub>SD</sub>     | Diode forward voltage          | I <sub>S</sub> =1A, V <sub>GS</sub> = 0V                          |     |     | 1    | V    |

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